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#### SLPS198B-AUGUST 2009-REVISED APRIL 2010

# N-Channel NexFET<sup>™</sup> Power MOSFET

Check for Samples: CSD16404Q5A

# **FEATURES**

- Ultralow Q<sub>g</sub> and Q<sub>gd</sub>
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

## **APPLICATIONS**

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Control FET Applications

# DESCRIPTION

The NexFET<sup>™</sup> power MOSFET has been designed to minimize losses in power conversion applications.





### PRODUCT SUMMARY

V <sub>DS</sub>	Drain to Source Voltage	25	V	
Qg	Gate Charge Total (4.5V)	6.5	nC	
$Q_{gd}$	Gate Charge Gate to Drain	1.7	nC	
P	Drain to Source On Resistance	$V_{GS} = 4.5V$	5.7	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = 10V 4.1		mΩ
V <sub>GS(th)</sub>	Threshold Voltage	1.8		V

#### **ORDERING INFORMATION**

Device	Package	Media	Qty	Ship
CSD16404Q5A	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

#### **ABSOLUTE MAXIMUM RATINGS**

$T_A = 2$	5°C unless otherwise stated	VALUE	UNIT
V <sub>DS</sub>	Drain to Source Voltage	25	V
$V_{GS}$	Gate to Source Voltage	+16 / -12	V
	Continuous Drain Current, $T_C = 25^{\circ}C$	81	А
ID	Continuous Drain Current <sup>(1)</sup>	21	А
I <sub>DM</sub>	Pulsed Drain Current, $T_A = 25^{\circ}C^{(2)}$	135	А
PD	Power Dissipation <sup>(1)</sup>	3	W
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C
E <sub>AS</sub>	Avalanche Energy, single pulse $I_D = 40A$ , L = 0.1mH, $R_G = 25\Omega$	80	mJ

(1)  $R_{\theta JA} = 41^{\circ}C/W$  on 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.

(2) Pulse duration  $\leq 300 \mu s$ , duty cycle  $\leq 2\%$ 



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

# **ELECTRICAL CHARACTERISTICS**

#### $T_A = 25^{\circ}C$ , unless otherwise specified

PARAMETER		TEST CONDITIONS	MIN TYP	MAX	UNIT
Static Cl	haracteristics				
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$	25		V
I <sub>DSS</sub>	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$		1	μA
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +16/-12V$		100	nA
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.4 1.8	2.1	V
D	Drain to Source On Registeres	$V_{GS} = 4.5V, I_D = 20A$	5.7	7.2	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 10V, I_D = 20A$	4.1	5.1	mΩ
9 <sub>fs</sub>	Transconductance	$V_{DS} = 15V, I_{D} = 20A$	57		S
Dynamic	Characteristics		·		
C <sub>ISS</sub>	Input Capacitance		940	1220	pF
C <sub>OSS</sub>	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V$ , f = 1MHz	810	1050	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance		62	80	pF
R <sub>g</sub>	Series Gate Resistance		0.9	1.8	Ω
Qg	Gate Charge Total (4.5V)		6.5	8.5	nC
Q <sub>gd</sub>	Gate Charge Gate to Drain		1.7		nC
Q <sub>gs</sub>	Gate Charge Gate to Source	$V_{\rm DS} = 12.5 V, I_{\rm D} = 20 A$	3		nC
Q <sub>g(th)</sub>	Gate Charge at Vth		1.5		nC
Q <sub>OSS</sub>	Output Charge	$V_{DS} = 13V, V_{GS} = 0V$	16		nC
t <sub>d(on)</sub>	Turn On Delay Time		7.8		ns
t <sub>r</sub>	Rise Time	V <sub>DS</sub> = 12.5V, V <sub>GS</sub> = 4.5V,	13.4		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$I_D = 20A, R_G = 2\Omega$	8.4		ns
t <sub>f</sub>	Fall Time		4.6		ns
Diode Cl	haracteristics			1	
V <sub>SD</sub>	Diode Forward Voltage	$I_{\rm S} = 20 {\rm A}, V_{\rm GS} = 0 {\rm V}$	0.85	1	V
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{DD}$ = 13V, I <sub>F</sub> = 20A, di/dt = 300A/µs	20		nC
t <sub>rr</sub>	Reverse Recovery Time	V <sub>DD</sub> = 13V, I <sub>F</sub> = 20A, di/dt = 300A/µs	22		ns

# THERMAL CHARACTERISTICS

 $T_A = 25^{\circ}C$ , unless otherwise specified

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\thetaJC}$	Thermal Resistance Junction to Case <sup>(1)</sup>			3.3	°C/W
$R_{\thetaJA}$	Thermal Resistance Junction to Ambient <sup>(1)</sup> <sup>(2)</sup>			52	°C/W

 $R_{\theta JC}$  is determined with the device mounted on a 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB.  $R_{\theta JC}$  is specified by design, whereas  $R_{\theta JA}$  is determined by the user's board design. Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu. (1)

(2)



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# CSD16404Q5A

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GATE 🔘 🔘 Source

DRAIN

M0137-02



Max  $R_{\theta JA} = 120^{\circ}C/W$ when mounted on minimum pad area of 2-oz. (0.071-mm thick) Cu.

## **TYPICAL MOSFET CHARACTERISTICS**



Figure 1. Transient Thermal Impedance

12

10

8

6

4

2

0

0

V<sub>G</sub> – Gate Voltage – V

 $I_D = 20A$ 

3

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# **TYPICAL MOSFET CHARACTERISTICS (continued)**

#### $T_A = 25^{\circ}C$ , unless otherwise specified







**Figure 3. Transfer Characteristics** 



4

2

0

0



Figure 7. On-State Resistance vs. Gate to Source Voltage

6

V<sub>GS</sub> – Gate to Source Voltage – V

 $T_C = 25^{\circ}C$ 

4

2

4

8

10

12

G006



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## **TYPICAL MOSFET CHARACTERISTICS (continued)**

#### $T_A = 25^{\circ}C$ , unless otherwise specified





Figure 8. Normalized On-State Resistance vs. Temperature



Figure 10. Maximum Safe Operating Area





Figure 11. Single Pulse Unclamped Inductive Switching



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# **MECHANICAL DATA**

# **Q5A Package Dimensions**







Top View

Side View

Bottom View



**Front View** 

M0135-01

DIM		MILLIMETERS	
DIM	MIN	NOM	MAX
А	0.90	1.00	1.10
b	0.33	0.41	0.51
С	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70 5.75		5.80
E2	3.38	3.58	3.78
е		1.27 BSC	
Н	0.41	0.51	0.61
К	1.10		
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
θ	0°		12°



# CSD16404Q5A

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For recommended circuit layout for PCB designs, see application note SLPA005 - Reducing Ringing Through PCB Layout Techniques.

### **Q5A Tape and Reel Information**



Notes: 1. 10-sprocket hole-pitch cumulative tolerance ±0.22

- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- 6. MSL1 260°C (IR and convection) PbF reflow compatible

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## **REVISION HISTORY**

Changes from Original (August 2009) to Revision A	Page
<ul> <li>Changed Figure 10 - Maximum Safe Operating Area, Drain Current top scale From: 100ms To: 100µs</li> </ul>	5
Changes from Revision A (September 2009) to Revision B	Page
Deleted the Package Marking Information section	

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# PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION

#### REEL DIMENSIONS

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#### TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

## TAPE AND REEL INFORMATION

\*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16404Q5A	SON	DQJ	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

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# PACKAGE MATERIALS INFORMATION

8-Sep-2012



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD16404Q5A	SON	DQJ	8	2500	340.0	340.0	38.0

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